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Patent Number: WO0063957

Publication date: 2000-10-26

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Requested Patent: ☐ WO0063957

Application Number: WO2000KR00310 20000406

Priority Number(s): KR19990011877 19990406

IPC Classification: H01L21/205

EC Classification: C30B25/14, C23C16/455, C23C16/515, C23C16/56, C30B25/10B

EC Classification: C30B25/14; C23C16/455; C23C16/515; C23C16/56; C30B25/10B

Equivalents: ☐ EP1092233 (WO0063957), KR273473

Abstract

The invention provides a method of forming a thin film for semiconductor or flat panel display devices. In a chemical vapor deposition method which supplies cyclically reactant gases and a purge gas which prevents the gas-phase reaction between the reactant gases, generating plasma on a substrate synchronously with the gas supply cycle can form a thin film at low temperature and reduce particle generation at exhaust.